Galia Pozina

List of Publications by Year
in descending order

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222	4,302	136740	138251
papers	citations	32 h-index	58 g-index

226	226	226	4692
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Opposite Sign of Polarization Splitting in Ultrastrongly Coupled Organic Tamm Plasmon Structures. Journal of Physical Chemistry C, 2021, 125, 8376-8381.	1.5	7
2	Quantum analysis of luminescence of an exciton in a meso-cavity. Optics Express, 2021, 29, 20724.	1.7	5
3	Doping of Î²â€Ga₂O₃ Layers by Zn Using Halide Vaporâ€Phase Epitaxy Process. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100486.	0.8	5
4	Synthesis of Mg-doped ZnO NPs via a chemical low-temperature method and investigation of the efficient photocatalytic activity for the degradation of dyes under solar light. Solid State Sciences, 2020, 99, 106053.	1.5	46
5	Optical properties of AlGaN/GaN epitaxial layers grown on different face GaN substrates. Materials Letters, 2020, 263, 127229.	1.3	10
6	Emission Properties of GaN Planar Hexagonal Microcavities. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900894.	0.8	5
7	Study of Dislocations in Homoepitaxially and Heteroepitaxially Grown AlN Layers. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000465.	0.8	3
8	Control of the surface plasmon dispersion and Purcell effect at the metamaterial-dielectric interface. Scientific Reports, 2020, 10, 20828.	1.6	3
9	Single-emissive-layer all-perovskite white light-emitting diodes employing segregated mixed halide perovskite crystals. Chemical Science, 2020, 11, 11338-11343.	3.7	18
10	Efficient UV Luminescence from Organic-Based Tamm Plasmon Structures Emitting in the Strong-Coupling Regime. Journal of Physical Chemistry C, 2020, 124, 21656-21663.	1.5	10
11	Development of Î²-Ga2O3 layers growth on sapphire substrates employing modeling of precursors ratio in halide vapor phase epitaxy reactor. Scientific Reports, 2020, 10, 22261.	1.6	17
12	Strong Coupling of Excitons in Hexagonal GaN Microcavities. Semiconductors, 2020, 54, 127-130.	0.2	0
13	Perovskite-molecule composite thin films for efficient and stable light-emitting diodes. Nature Communications, 2020, 11, 891.	5.8	83
14	Weak and strong coupling of photons and excitons in planar meso-cavities. Optics Express, 2020, 28, 12688.	1.7	4
15	Proposal for a photoacoustic ultrasonic generator based on Tamm plasmon structures. Optics Express, 2020, 28, 26161.	1.7	7
16	Enhancement of light emission in Bragg monolayer-thick quantum well structures. Scientific Reports, 2019, 9, 10162.	1.6	0
17	Revising of the Purcell effect in periodic metal-dielectric structures: the role of absorption. Scientific Reports, 2019, 9, 9604.	1.6	16
18	Optical Cavity Based on GaN Planar Nanowires Grown by Selective Area Metalâ€Organic Vapor Phase Epitaxy. Physica Status Solidi (B): Basic Research, 2019, 256, 1800631.	0.7	5

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19	Graphene-based plasmonic nanocomposites for highly enhanced solar-driven photocatalytic activities. RSC Advances, 2019, 9, 30585-30598.	1.7	17
20	Purcell Effect and Nonlinear Behavior of the Emission in a Periodic Structure Composed of InAs Monolayers Embedded in a GaAs Matrix. Annalen Der Physik, 2019, 531, 1800388.	0.9	0
21	Purcell Effect in Tamm Plasmon Structures with QD Emitter. Semiconductors, 2018, 52, 452-457.	0.2	1
22	Polyethylene glycol-doped BiZn₂VO₆as a high-efficiency solar-light-activated photocatalyst with substantial durability toward photodegradation of organic contaminations. RSC Advances, 2018, 8, 37480-37491.	1.7	6
23	Optical studies of InAs/GaAs monolayer Bragg superlattices. Journal of Physics: Conference Series, 2018, 1124, 081045.	0.3	0
24	Experimental Study of Spontaneous Emission in the Bragg Multiple Quantum Wells Structure of InAs Monolayers Embedded in a GaAs Matrix. Semiconductors, 2018, 52, 1822-1826.	0.2	0
25	Control of spontaneous emission rate in Tamm plasmon structures. , 2018, , .		0
26	Different regimes of the Purcell effect in disordered photonic crystals. Journal of Physics Condensed Matter, 2018, 30, 435304.	0.7	3
27	Synthesis of ZnO nanoparticles by co-precipitation method for solar driven photodegradation of Congo red dye at different pH. Photonics and Nanostructures - Fundamentals and Applications, 2018, 32, 11-18.	1.0	174
28	FÃ¶rster Energy Transfer in Arrays of Epitaxial CdSe/ZnSe Quantum Dots Involving Bright and Dark Excitons. Physics of the Solid State, 2018, 60, 1590-1594.	0.2	3
29	Ring resonator optical modes in InGaN/GaN structures grown on micro-cone-patterned sapphire substrates. Journal of Physics: Conference Series, 2018, 993, 012020.	0.3	0
30	Design rules for minimizing voltage losses in high-efficiency organic solar cells. Nature Materials, 2018, 17, 703-709.	13.3	701
31	Approach to high quality GaN lateral nanowires and planar cavities fabricated by focused ion beam and metal-organic vapor phase epitaxy. Scientific Reports, 2018, 8, 7218.	1.6	11
32	Site-Controlled Growth of GaN Nanorods with Inserted InGaN Quantum Wells on Î¼-Cone Patterned Sapphire Substrates by Plasma-Assisted MBE. Semiconductors, 2018, 52, 667-670.	0.2	1
33	Purcell effect in a disordered photonic crystals. , 2018, , .		0
34	Experimental Study of Spontaneous Emission in Bragg Multiple- Quantum-Well Structures with InAs Single-Layer Quantum Wells. Semiconductors, 2018, 52, 877-880.	0.2	0
35	Emission properties of Ga2O3 nano-flakes: effect of excitation density. Scientific Reports, 2017, 7, 42132.	1.6	42
36	Near band gap luminescence in hybrid organic-inorganic structures based on sputtered GaN nanorods. Scientific Reports, 2017, 7, 1170.	1.6	5

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37	An effective low-temperature solution synthesis of Co-doped [0001]-oriented ZnO nanorods. Journal of Applied Physics, 2017, 121, .	1.1	9
38	Polarization of stacking fault related luminescence in GaN nanorods. AIP Advances, 2017, 7, .	0.6	8
39	Recombination dynamics in arrays of II-VI epitaxial quantum dots with FÃ¶rster resonance energy transfer. Physica Status Solidi (B): Basic Research, 2017, 254, 1600414.	0.7	0
40	Enhancement of spontaneous emission in Tamm plasmon structures. Scientific Reports, 2017, 7, 9014.	1.6	51
41	Site-controlled GaN nanocolumns with InGaN insertions grown by MBE. Journal of Physics: Conference Series, 2017, 917, 032032.	0.3	3
42	Suppression of slow decaying emission in II-VI quantum dots with FÃ¶rster resonance energy transfer. Journal of Physics: Conference Series, 2017, 917, 062048.	0.3	1
43	AlGaN Nanostructures with Extremely High Room-Temperature Internal Quantum Efficiency of Emission Below 300Ânm. Journal of Electronic Materials, 2017, 46, 3888-3893.	1.0	3
44	Nonlinear behavior of the emission in the periodic structure of InAs monolayers embedded in a GaAs matrix. Physica Status Solidi (B): Basic Research, 2017, 254, 1600402.	0.7	9
45	Seed layer synthesis effect on the concentration of interface defects and emission spectra of ZnO nanorods/pâ€GaN lightâ€emitting diode. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600333.	0.8	6
46	Coexistence of type-I and type-II band line-ups in 1-2 monolayer thick GaN/AlN single quantum wells. Journal of Physics: Conference Series, 2017, 917, 062050.	0.3	0
47	Recombination dynamics in heterostructures with two planar arrays of II-VI quantum dots. Journal of Physics: Conference Series, 2016, 741, 012153.	0.3	2
48	Structural properties and vertical transport in ZnSe/CdSe superlattices grown on an In0.3Ga0.7As metamorphic buffer layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 503-506.	0.8	0
49	Electronic properties of defects in highâ€fluence electronâ€irradiated bulk GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 521-526.	0.7	3
50	Exciton recombination in spontaneously formed and artificial quantum wells Al_xGa_{1â€x}N/Al_yGa_{1â€y}N (x<yâ¼0.8). Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 232-238.	0.8	1
51	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. Journal of Applied Physics, 2016, 119, .	1.1	8
52	Influence of ZnO seed layer precursor molar ratio on the density of interface defects in low temperature aqueous chemically synthesized ZnO nanorods/GaN light-emitting diodes. Journal of Applied Physics, 2016, 119, .	1.1	30
53	III-nitride tunable cup-cavities supporting quasi whispering gallery modes from ultraviolet to infrared. Scientific Reports, 2016, 5, 17970.	1.6	13
54	Deep level study of Mg-doped GaN using deep level transient spectroscopy and minority carrier transient spectroscopy. Physical Review B, 2016, 94, .	1.1	12

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55	AlGaN nanostructures with extremely high quantum yield at 300 K. Physics of the Solid State, 2016, 58, 2261-2266.	0.2	0
56	IIIâ€nitride microcrystal cavities with quasi whispering gallery modes grown by molecular beam epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 845-852.	0.7	5
57	Super-radiant mode in InAsâ€"monolayerâ€"based Bragg structures. Scientific Reports, 2015, 5, 14911.	1.6	22
58	Effect of precursor solutions stirring on deep level defects concentration and spatial distribution in low temperature aqueous chemical synthesis of zinc oxide nanorods. AIP Advances, 2015, 5, .	0.6	13
59	Dislocation related droop in InGaN/GaN light emitting diodes investigated via cathodoluminescence. Applied Physics Letters, 2015, 107, .	1.5	39
60	Time-resolved photoluminescence properties of hybrids based on inorganic AlGaN/GaN quantum wells and colloidal ZnO nanocrystals. Superlattices and Microstructures, 2015, 87, 38-41.	1.4	2
61	Properties of GaN layers grown on N-face free-standing GaN substrates. Journal of Crystal Growth, 2015, 413, 81-85.	0.7	3
62	Dynamic properties of excitons in ZnO/AlGaN/GaN hybrid nanostructures. Scientific Reports, 2015, 5, 7889.	1.6	6
63	Optical and structural properties of sulfur-doped ELOG InP on Si. Journal of Applied Physics, 2015, 117, .	1.1	5
64	Stacking fault related luminescence in GaN nanorods. Nanotechnology, 2015, 26, 355203.	1.3	23
65	AlGaN Quantum Well Heterostructures for Mid-Ultraviolet Emitters with Improved Room Temperature Quantum Efficiency. Acta Physica Polonica A, 2014, 126, 1140-1142.	0.2	2
66	Decoration of ZnO Nanorods with Coral Reefs like NiO Nanostructures by the Hydrothermal Growth Method and Their Luminescence Study. Materials, 2014, 7, 430-440.	1.3	15
67	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. Applied Physics Letters, 2014, 105, .	1.5	21
68	Properties of the main Mg-related acceptors in GaN from optical and structural studies. Journal of Applied Physics, 2014, 115, 053507.	1.1	42
69	Optical properties of C-doped bulk GaN wafers grown by halide vapor phase epitaxy. Journal of Applied Physics, 2014, 116, .	1.1	24
70	High quality InP nanopyramidal frusta on Si. CrystEngComm, 2014, 16, 4624-4632.	1.3	4
71	Defect reduction in heteroepitaxial InP on Si by epitaxial lateral overgrowth. Materials Express, 2014, 4, 41-53.	0.2	7
72	Single and double bosonic stimulation of THz emission in polaritonic systems. Scientific Reports, 2014, 4, 5444.	1.6	17

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73	Atom probe tomography study of Mg-doped GaN layers. Nanotechnology, 2014, 25, 275701.	1.3	20
74	Synthesis of CuO/ZnO Composite Nanostructures, Their Optical Characterization and Valence Band Offset Determination by X-Ray Photoelectron Spectroscopy. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 348-356.	0.1	12
75	Optimization of low temperature GaN buffer layers for halide vapor phase epitaxy growth of bulk GaN. Journal of Crystal Growth, 2013, 366, 61-66.	0.7	27
76	Suppression of the quantum-confined Stark effect in AlxGa1â^'xN/AlyGa1â^'yN corrugated quantum wells. Journal of Applied Physics, 2013, 114, 124306.	1.1	10
77	Surface potential effect on excitons in AlGaN/GaN quantum well structures. Applied Physics Letters, 2013, 102, 082110.	1.5	10
78	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. Thin Solid Films, 2013, 543, 11-15.	0.8	11
79	Study of planar defect filtering in InP grown on Si by epitaxial lateral overgrowth. Optical Materials Express, 2013, 3, 1960.	1.6	25
80	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	36
81	Correlation between Si doping and stacking fault related luminescence in homoepitaxial m-plane GaN. Applied Physics Letters, 2013, 103, .	1.5	17
82	Luminescence of Acceptors in Mg-Doped GaN. Japanese Journal of Applied Physics, 2013, 52, 08JJ03.	0.8	19
83	Optical and structural studies of homoepitaxially grown m-plane GaN. Applied Physics Letters, 2012, 100, .	1.5	11
84	The effect of exciton dimensionality on resonance energy transfer: advances for organic color converters in hybrid inorganic/organic LEDs. Proceedings of SPIE, 2012, , .	0.8	1
85	Effect of the Surface Morphology of Seed and Mask Layers on InP Grown on Si by Epitaxial Lateral Overgrowth. Journal of Electronic Materials, 2012, 41, 2345-2349.	1.0	16
86	Growth of GaN nanotubes by halide vapor phase epitaxy. Nanotechnology, 2011, 22, 085602.	1.3	25
87	Dependence of Resonance Energy Transfer on Exciton Dimensionality. Physical Review Letters, 2011, 107, 236805.	2.9	42
88	Luminescence related to high density of Mg-induced stacking faults in homoepitaxially grown GaN. Physical Review B, 2011, 84, .	1.1	34
89	Morphological evolution during epitaxial lateral overgrowth of indium phosphide on silicon. Journal of Crystal Growth, 2011, 332, 27-33.	0.7	18
90	Photoluminescence of Mgâ€doped mâ€plane GaN grown by MOCVD on bulk GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1532-1534.	0.8	6

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91	Delay and distortion of slow light pulses by excitons in ZnO. Physical Review B, 2011, 84, .	1.1	15
92	Effect of silicon and oxygen doping on donor bound excitons in bulk GaN. Physical Review B, 2011, 84, .	1.1	38
93	Excitonic parameters of GaN studied by time-of-flight spectroscopy. Applied Physics Letters, 2011, 99, 101108.	1.5	6
94	Photoluminescence of Mg-doped m -plane GaN grown by MOCVD on bulk GaN substrates. Proceedings of SPIE, 2011, , .	0.8	2
95	Hetero-epitaxial indium phosphide on silicon. , 2010, , .		1
96	Optical Properties Of Metastable Shallow Acceptors In Mg-Doped GaN Layers Grown By Metal-Organic Vapor Phase Epitaxy. , 2010, , .		0
97	Surface Recombination in ZnO Nanorods Grown by Aqueous Chemical Methods. , 2010, , .		0
98	Mgâ€related acceptors in GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1850-1852.	0.8	11
99	Size dependent carrier recombination in ZnO nanocrystals. Applied Physics Letters, 2010, 97, .	1.5	32
100	Transient photoluminescence of shallow donor bound excitons in GaN. Physical Review B, 2010, 82, .	1.1	37
101	Heteroepitaxial growth of Indium phosphide from nano-openings made by masking on a Si(001) wafer. , 2010, , .		0
102	Indirect optical transition due to surface band bending in ZnO nanotubes. Journal of Applied Physics, 2010, 108, 103513.	1.1	27
103	DAP emission band in a carbon doped (1â€101)GaN grown on (001)Si substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S772.	0.8	2
104	Phase transformation in Î¹- and Î³-Al2O3 coatings on cutting tool inserts. Surface and Coatings Technology, 2009, 203, 1682-1688.	2.2	43
105	Growth and characterization of thick GaN layers grown by halide vapour phase epitaxy on lattice-matched AlInN templates. Journal of Crystal Growth, 2009, 311, 292-297.	0.7	7
106	Evidence for Two Mg Related Acceptors in GaN. Physical Review Letters, 2009, 102, 235501.	2.9	108
107	Reducing Thermal Resistance of AlGaN/GaN Electronic Devices Using Novel Nucleation Layers. IEEE Electron Device Letters, 2009, 30, 103-106.	2.2	59
108	Phase identification in Î³- and Î¹-alumina coatings by cathodoluminescence. Scripta Materialia, 2009, 61, 379-382.	2.6	3

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109	Modeling, optimization, and growth of GaN in a vertical halide vapor-phase epitaxy bulk reactor. Journal of Crystal Growth, 2008, 310, 906-910.	0.7	12
110	Time-resolved spectroscopy of freestanding GaN layers grown by halide vapour phase epitaxy. Superlattices and Microstructures, 2008, 43, 605-609.	1.4	4
111	Effects of hydrogen on the optical properties of ZnCdOâˆ•ZnO quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261912.	1.5	22
112	Time-resolved photoluminescence properties of AlGaN/AlN/GaN high electron mobility transistor structures grown on 4H-SiC substrate. Journal of Applied Physics, 2008, 104, 113513.	1.1	1
113	Resonant Light Delay in GaN with Ballistic and Diffusive Propagation. Physical Review Letters, 2008, 100, 087402.	2.9	24
114	Effect of annealing on metastable shallow acceptors in Mg-doped GaN layers grown on GaN substrates. Applied Physics Letters, 2008, 92, 151904.	1.5	11
115	Metastable behavior of the UV luminescence in Mg-doped GaN layers grown on quasibulk GaN templates. Applied Physics Letters, 2007, 91, .	1.5	32
116	Recombination dynamics and lasing in ZnOâˆ•ZnMgO single quantum well structures. Applied Physics Letters, 2007, 91, 201104.	1.5	19
117	Dynamics of bound excitons versus thickness in freestanding GaN wafers grown by halide vapor phase epitaxy. Applied Physics Letters, 2007, 90, 221904.	1.5	16
118	Metastability of the UV luminescence in Mg-doped GaN layers grown by MOVPE on quasi-bulk GaN templates. Physica B: Condensed Matter, 2007, 401-402, 302-306.	1.3	6
119	Hydride vapour phase epitaxy growth and characterization of thick GaN using a vertical HVPE reactor. Journal of Crystal Growth, 2007, 300, 32-36.	0.7	36
120	Mechanism for radiative recombination in ZnCdO alloys. Applied Physics Letters, 2007, 90, 261907.	1.5	23
121	Growth of bulk GaN in a vertical hydride vapour phase epitaxy reactor. Superlattices and Microstructures, 2006, 40, 205-213.	1.4	28
122	Optical investigation of AlGaN/GaN quantum wells and superlattices. Physica Status Solidi A, 2004, 201, 2251-2258.	1.7	1
123	Time resolved photoluminescence study of Si modulation doped GaN/Al0.07Ga0.93N multiple quantum wells. Physica Status Solidi (B): Basic Research, 2004, 241, 1124-1133.	0.7	8
124	Radiative recombination processes in Al0.07Ga0.93N/GaN multiple quantum well structures, role of hole localisation. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2500-2503.	0.8	1
125	SiC Crystal Growth by HTCVD. Materials Science Forum, 2004, 457-460, 9-14.	0.3	56
126	Influence of polarization fields and depletion fields on photoluminescence of AlGaN/GaN multiple quantum well structures. Physica Status Solidi (B): Basic Research, 2003, 237, 353-364.	0.7	24

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127	Effect of n-type modulation doping on the photoluminescence of GaN/Al0.07Ga0.93N multiple quantum wells. Applied Physics Letters, 2002, 80, 1373-1375.	1.5	13
128	Photoluminescence and Electroluminescence Characterization of In_xGa_{1-x}N/In_yGa_{1-y}N0.3 Multiple Quantum Well Light Emitting Diodes. Materials Science Forum, 2002, 389-393, 1493-1496.		0
129	Characterisation and Defects in Silicon Carbide. Materials Science Forum, 2002, 389-393, 9-14.	0.3	42
130	Characterization of Bulk and Epitaxial SiC Material Using Photoluminescence Spectroscopy. Materials Science Forum, 2002, 389-393, 593-596.	0.3	18
131	Photoluminescence in n-doped In0.1Ga0.9N/In0.01Ga0.99N multiple quantum wells. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	10
132	<title>Optical properties of InGaN/GaN and AlGaN/GaN multiple quantum well structures</title>. , 2002, , .		0
133	Time-resolved studies of photoluminescence in GaNxP1â^'x alloys: Evidence for indirect-direct band gap crossover. Applied Physics Letters, 2002, 81, 52-54.	1.5	83
134	Optical investigation of CdSe/ZnSe quantum nanostructures. Semiconductor Science and Technology, 2002, 17, 173-177.	1.0	4
135	Interface Effects in Type-II CdSe/BeTe Quantum Dots. Physica Status Solidi (B): Basic Research, 2002, 229, 489-492.	0.7	6
136	Optical Study of AlGaN/GaN Multiple Quantum Well Structures Grown on Laterally Overgrown GaN Templates. Physica Status Solidi A, 2002, 190, 107-111.	1.7	1
137	Photoluminescence of Excitons in InxGa1?xN/InyGa1?yN Multiple Quantum Wells. Physica Status Solidi A, 2002, 190, 161-166.	1.7	1
138	Influence of Depletion Fields on Photoluminescence of n-Doped InGaN/GaN Multiple Quantum Well Structures. Physica Status Solidi A, 2002, 192, 21-26.	1.7	3
139	Optical characterization of III-nitrides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 112-122.	1.7	28
140	Evidence for type I band alignment in GaNAs/GaAs quantum structures by optical spectroscopies. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1074-1077.	1.3	2
141	Photoluminescence of Excitons in n-Type In0.11Ga0.89N/In0.01Ga0.99N Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 2001, 693, 733.	0.1	0
142	Characterization of Red Emission in Nominally Undoped Hydride Vapor Phase Epitaxy GaN. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	15
143	In-plane and in-depth nonuniformities in defect distribution in GaN and InGaN epilayers. Physica B: Condensed Matter, 2001, 308-310, 102-105.	1.3	3
144	Optical properties of GaNAs/GaAs structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 143-147.	1.7	15

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145	Time-resolved optical properties of GaN grown by metalorganic vapor phase epitaxy with indium surfactant. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 137-139.	1.7	4
146	Magneto-photoluminescence studies of Cd(Mn)Se/Zn(Mn)Se diluted magnetic nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 362-367.	1.3	2
147	Optical Characterization of InGaN/GaN MQW Structures without In Phase Separation. Physica Status Solidi (B): Basic Research, 2001, 228, 157-160.	0.7	6
148	Radiative and Nonradiative Exciton Lifetimes in GaN Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 485-488.	0.7	3
149	The 3.466 eV Bound Exciton in GaN. Physica Status Solidi (B): Basic Research, 2001, 228, 489-492.	0.7	8
150	Time-Resolved Photoluminescence in Strained GaN Layers. Physica Status Solidi A, 2001, 183, 151-155.	1.7	5
151	Photoluminescence of InGaN/GaN multiple quantum wells grown by mass transport. Journal of Crystal Growth, 2001, 230, 473-476.	0.7	2
152	Luminescence of InGaN/GaN Multiple Quantum Wells Grown by Mass-Transport. Materials Science Forum, 2001, 353-356, 791-794.	0.3	1
153	Time-resolved spectroscopy of strained GaN/AlN/6Hâ€“SiC heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 1062-1064.	1.5	14
154	Radiative and Nonradiative Exciton Lifetimes in GaN Grown by Molecular Beam Epitaxy. , 2001, 228, 485.		1
155	The 3.466 eV Bound Exciton in GaN. , 2001, 228, 489.		1
156	Recombination Processes of GaNAs/GaAs structures: Effect of Rapid Thermal Annealing. Springer Proceedings in Physics, 2001, , 559-560.	0.1	0
157	Multiple Peak Spectra from InGaN/GaN Multiple Quantum Wells. Physica Status Solidi A, 2000, 180, 85-89.	1.7	4
158	MBE growth and properties of bulk BeCdSe alloys and digital (BeSe:CdSe)/ZnSe quantum wells. Journal of Crystal Growth, 2000, 214-215, 109-114.	0.7	22
159	Dynamics of excitons near the mobility edge in CdSe/ZnSe superlattices. Journal of Crystal Growth, 2000, 214-215, 806-809.	0.7	2
160	Group III-nitride based hetero and quantum structures. Progress in Quantum Electronics, 2000, 24, 239-290.	3.5	94
161	Light emitting SiGe/i-Si/Si:Er:O tunneling diodes prepared by molecular beam epitaxy. Thin Solid Films, 2000, 369, 414-418.	0.8	6
162	Luminescence and microstructure of Er/O co-doped Si structures grown by MBE using Er and SiO evaporation. Materials Science in Semiconductor Processing, 2000, 3, 523-528.	1.9	7

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163	Excitons as a probe of interface morphology in Cd(Zn)Se/ZnSe heterostructures. Applied Surface Science, 2000, 166, 278-283.	3.1	4
164	Type I band alignment in theGaNxAs1â˜'x/GaAsquantum wells. Physical Review B, 2000, 63, .	1.1	57
165	InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy with mass transport. Applied Physics Letters, 2000, 77, 1638-1640.	1.5	14
166	Optical spectroscopy of GaN grown by metalorganic vapor phase epitaxy using indium surfactant. Applied Physics Letters, 2000, 76, 3388-3390.	1.5	28
167	Origin of multiple peak photoluminescence in InGaN/GaN multiple quantum wells. Journal of Applied Physics, 2000, 88, 2677-2681.	1.1	54
168	Mechanism for rapid thermal annealing improvements in undoped GaNxAs1â˜'x/GaAs structures grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 2325-2327.	1.5	95
169	Radiative recombination in In_{0.15}Ga_{0.85}N/GaN multiple quantum well structures. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	34
170	Bound exciton dynamics in GaN grown by hydride vapor-phase epitaxy. Applied Physics Letters, 1999, 75, 4124-4126.	1.5	49
171	Optical and Transport Properties of CdSe/ZnSe Self-Organized Nanostructures: 1-Dimensional versus 3-Dimensional Quantum Confinement. Japanese Journal of Applied Physics, 1999, 38, 566-569.	0.8	20
172	Effect of Si doping on structural, photoluminescence and electrical properties of GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 195-197.	1.7	7
173	Optical properties of nanostructures self-organized in CdSe/ZnSe fractional monolayer superlattices. Journal of Crystal Growth, 1999, 201-202, 1231-1234.	0.7	2
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175	Mechanism for Light Emission in GaNAs/GaAs Structures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 125-129.	0.7	9
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